PNP General Purpose Transistor

The MMBT2907AM3T5G device is a spin-off of our popular SOT-23 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-723 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- Reduces Board Space
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	-60	Vdc
Collector - Base Voltage	V _{CBO}	-60	Vdc
Emitter – Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous	I _C	-600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	265 2.1	mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	470	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	640 5.1	mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	195	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

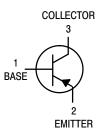
1

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



ON Semiconductor®

www.onsemi.com



SOT-723 CASE 631AA 2 STYLE 1

AC M

MARKING

AC = Specific Device Code M = Date Code

ORDERING INFORMATION

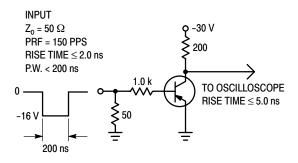
Device	Package	Shipping [†]
MMBT2907AM3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel
NSVMMBT2907AM3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				1	1
Collector-Emitter Breakdown Voltage (Note 3) $(I_C = -10 \text{ mAdc}, I_B = 0)$		V _{(BR)CEO}	-60	_	Vdc
Collector – Base Breakdown Voltage $(I_C = -10 \mu Adc, I_E = 0)$		V _{(BR)CBO}	-60	-	Vdc
Emitter – Base Breakdown Voltage $(I_E = -10 \mu Adc, I_C = 0)$		V _{(BR)EBO}	-5.0	_	Vdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)		I _{CEX}	_	-50	nAdc
Collector Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -50 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$		Ісво	_ _	-0.010 -10	μAdc
Base Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)		I _{BL}	-	-50	nAdc
ON CHARACTERISTICS				•	
DC Current Gain $ \begin{aligned} &(I_C = -0.1 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -1.0 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -10 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -150 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \\ &(I_C = -500 \text{ mAdc, } V_{CE} = -10 \text{ Vdc}) \end{aligned} $		h _{FE}	75 100 100 100 50	- - - 300 -	-
Collector – Emitter Saturation Voltage (Note 3) ($I_C = -150$ mAdc, $I_B = -15$ mAdc) (Note 3) ($I_C = -500$ mAdc, $I_B = -50$ mAdc)		V _{CE(sat)}		-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage (Note 3) (I _C = -150 mAdc, I _B = -15 mAdc) (I _C = -500 mAdc, I _B = -50 mAdc)		V _{BE(sat)}	-	-1.3 -2.6	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (Notes 3, 4) (I _C = –50 mAdc, V _{CE} = –20 Vdc, f = 100 MHz)		f _T	200	-	MHz
Output Capacitance $(V_{CB} = -10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$		C _{obo}	_	8.0	pF
Input Capacitance $(V_{EB} = -2.0 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$		C _{ibo}	_	30	
SWITCHING CHARACTERISTICS					•
Turn-On Time		t _{on}	-	45	
Delay Time	$(V_{CC} = -30 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = -15 \text{ mAdc})$	t _d	_	10	
Rise Time	10 III (do)	t _r	_	40	
Turn-Off Time		t _{off}	_	100	ns
Storage Time	$(V_{CC} = -6.0 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = I_{B2} = -15 \text{ mAdc})$	t _s	_	80	
Fall Time		t _f	_	30	

- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%. 4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.





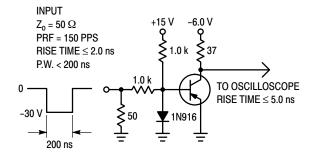


Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

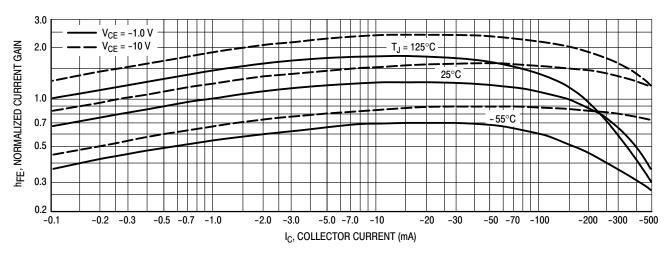


Figure 3. DC Current Gain

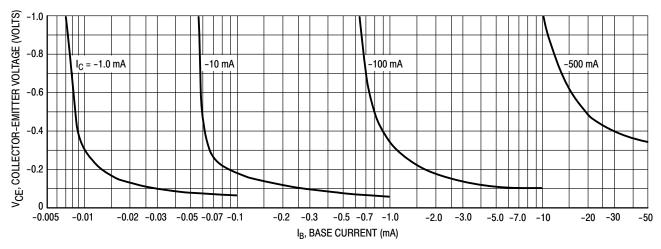


Figure 4. Collector Saturation Region

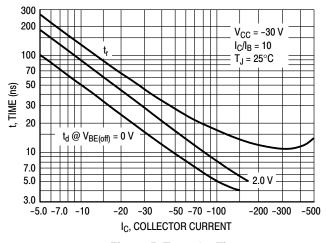


Figure 5. Turn-On Time

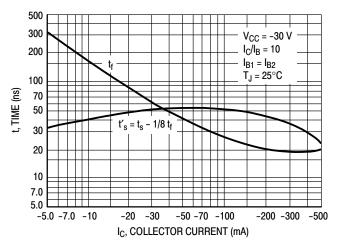
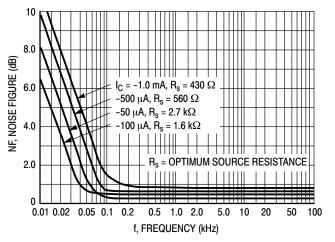


Figure 6. Turn-Off Time

TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

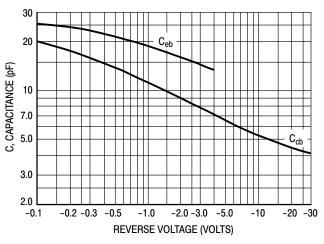
 V_{CE} = 10 Vdc, T_A = 25°C



8.0 NF, NOISE FIGURE (dB) 6.0 $I_C = -50 \mu A$ -100 μA -500 μA 4.0 1.0 mA 2.0 100 200 2.0 k 5.0 k 10 k 50 k 50 1.0 k 20 k R_s, SOURCE RESISTANCE (OHMS)

Figure 7. Frequency Effects

Figure 8. Source Resistance Effects



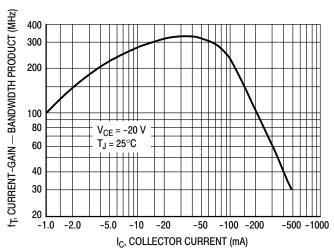
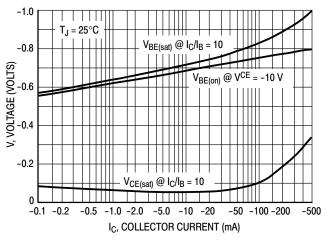


Figure 9. Capacitances

Figure 10. Current-Gain - Bandwidth Product



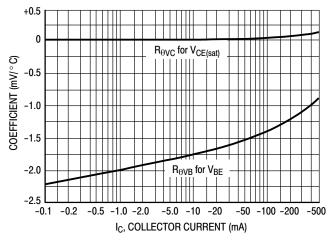
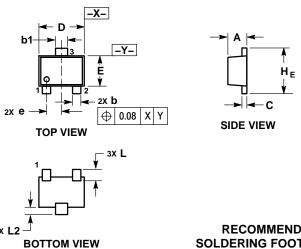


Figure 11. "On" Voltage

Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

SOT-723 CASE 631AA ISSUE D



NOTES

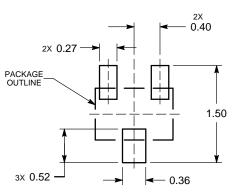
- 1. DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
С	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
е	0.40 BSC		
ΗE	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

STYLE 1:

PIN 1. BASE 2. EMITTER 3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative